

INDIUM COMPOUND AND METHOD FOR FORMING INDIUM-CONTAINING FILM USING SAID INDIUM COMPOUND

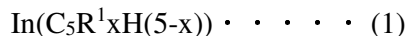
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Abstract

[**Problem**] to offer a process for forming an indium-containing film by ALD at high temperature which enables an indium compound to be employed without carrying out special pretreatment and, enables an indium-containing film with high throughput, and indium compounds for use in said process.

[**Solution**]

The process for forming an indium-containing film according to the present invention is characterized in that it includes (a) a step of placing a substrate inside a chamber, and (b) a step of introducing a gas which includes an indium compound represented by general formula (I) below, and (c) a first purging step, and (d) a step of introducing an oxygen-containing gas, and (e) a second purging step, and steps (b)-(e) are repeated, at a temperature of $\geq 225^{\circ}\text{C}$ and $\leq 400^{\circ}\text{C}$, until the desired thickness of the indium-containing film is obtained.



(Here, in general formula (1), x is an integer 1-5, and each R^1 is independently a C1-8 hydrocarbon group.)

[**Figure 1**]